

	Type	L #	Hits	Search Text	DBs	Time Stamp
1	BRS	L1	117	lee near heon.in.	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2005/01/0 5 06:24
2	BRS	L2	1932	438/257.ccls.	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2005/01/0 5 06:25
3	BRS	L3	7	2 and (magnetic near tunnel)	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2005/01/0 5 06:26

	Type	L #	Hits	Search Text	DBs	Time Stamp
4	BRS	L4	7	2 and (mtj)	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2005/01/0 5 06:26
5	BRS	L5	2444	(magnetic near tunnel or mtj)	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2005/01/0 5 06:47
6	BRS	L6	155	((magnetic near tunnel or mtj)) near25 (spacer or sidewall\$1)	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2005/01/0 5 06:41

	Type	L #	Hits	Search Text	DBs	Time Stamp
7	BRS	L7	25	((magnetic near tunnel or mtj)) near25 (side-wall\$1 or side near wall\$1)	US-PGPUB; USPAT; EPO; JPO; DERWE NT; IBM_T DB	2005/01/05 06:41
8	BRS	L8	117	((magnetic near tunnel or mtj)) near (stack)	US-PGPUB; USPAT; EPO; JPO; DERWE NT; IBM_T DB	2005/01/05 06:43
9	BRS	L9	1684	(magnetic near tunnel near junction)	US-PGPUB; USPAT; EPO; JPO; DERWE NT; IBM_T DB	2005/01/05 07:03

	Type	L #	Hits	Search Text	DBs	Time Stamp
10	BRS	L10	1336	(mtj)	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2005/01/0 5 07:03

	U	1	Document ID	Title	Current OR
1			US 20040253786 A1	Method for forming magnetic tunneling junction layer for magnetic random access memory	438/257
2			US 20040229430 A1	Fabrication process for a magnetic tunnel junction device	438/257
3			US 20040175887 A1	Magnetoresistive random access memory, and manufacturing method thereof	438/257
4			US 20040043562 A1	Magnetic memory cell having an annular data layer and a soft reference layer	438/257
5			US 6806127 B2	Method and structure for contacting an overlying electrode for a magnetoelectronics element	438/197
6			US 6803274 B2	Magnetic memory cell having an annular data layer and a soft reference layer	438/257
7			US 6777730 B2	Antiparallel magnetoresistive memory cells	257/295